# 2SA1890

### Silicon PNP epitaxial planer type

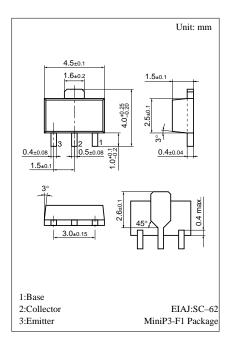
For low-frequency output amplification Complementary to 2SC5026

#### Features

- Low collector to emitter saturation voltage V<sub>CE(sat)</sub>.
- High collector to emitter voltage V<sub>CEO</sub>.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	-80	V
Collector to emitter voltage	V <sub>CEO</sub>	-80	V
Emitter to base voltage	V <sub>EBO</sub>	-5	V
Peak collector current	I <sub>CP</sub>	-1.5	А
Collector current	I <sub>C</sub>	-1	А
Collector power dissipation (T <sub>C</sub> =25°C)	$P_{C}^{*}$	1	W
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 ~ +150	°C

#### Absolute Maximum Ratings (Ta=25°C)



Marking symbol : 1Z

\* Printed circuit board: Copper foil area of 1cm<sup>2</sup> or more, and the board thickness of 1.7mm for the collector portion

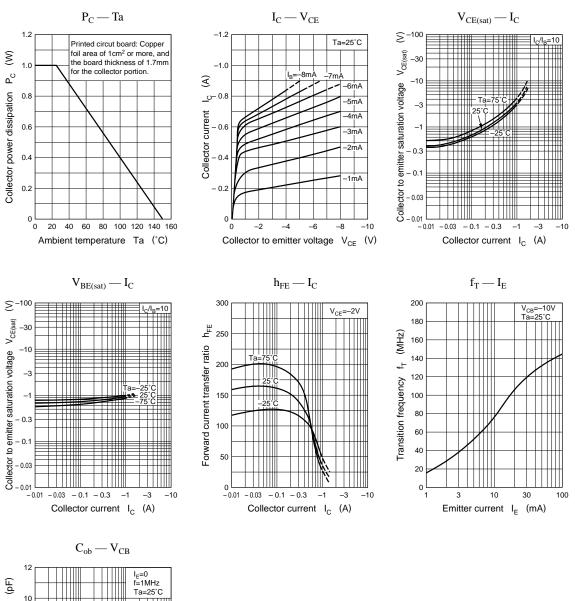
#### Electrical Characteristics (Ta=25°C)

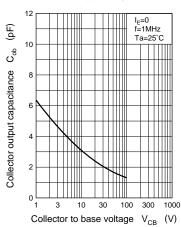
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = -40V, I_E = 0$			- 0.1	μΑ
Collector to base voltage	V <sub>CBO</sub>	$I_{\rm C} = -10 \mu A, I_{\rm E} = 0$	-80			V
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = -1  m A,  I_{\rm B} = 0$	-80			V
Emitter to base voltage	V <sub>EBO</sub>	$I_{\rm E} = -10 \mu A, I_{\rm C} = 0$	-5			V
	h <sub>FE1</sub> *1	$V_{CE} = -2V, I_C = -100mA$	120		340	
Forward current transfer ratio	h <sub>FE2</sub>	$V_{CE} = -2V, I_C = -500 \text{mA}^{*2}$	60			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -500 {\rm mA}, I_{\rm B} = -50 {\rm mA}^{*2}$		- 0.2	- 0.3	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = -500 {\rm mA}, I_{\rm B} = -50 {\rm mA}^{*2}$		- 0.85	-1.2	V
Transition frequency	f <sub>T</sub>	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		120		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10V, I_E = 0, f = 1MHz$		15	30	pF

\*2 Pulse measurement

\*1hFE1 Rank classification

Rank	Q	R
h <sub>FE1</sub>	120 ~ 240	170 ~ 340





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